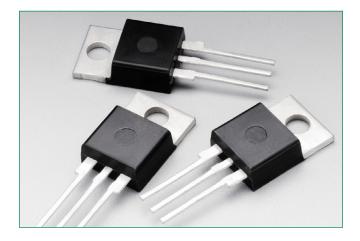
#### Thyristors Datasheet

Po

## BTB12-600TW3G Surface Mount – 600V



## **Additional Information**





3

Resources

Accessories

Samples

## Description

The BTB12 is designed for high performance full-wave AC control applications where high noise immunity and high commutating di/ dt are required.

#### **Features**

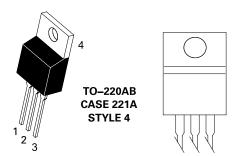
- Blocking Voltage to 600 V
- On-State Current Rating of 12 Amperes RMS at 80°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dV/dt 10 V/µs minimum at 125°C

## **Functional Diagram**

- Minimizes Snubber Networks for Protection
- Industry Standard TO-220AB Package
- High Commutating dl/dt 1.75 A/ms minimum at 110°C
- These are Pb–Free Devices



#### Pin Out



### Maximum Ratings (TJ = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, $T_{J} = -40^{\circ}$ to 110°C)	V <sub>drm</sub> , V <sub>rrm</sub>	600	V	
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 80$	0°C)	I <sub>T (RMS)</sub>	12	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>c</sub> = 25°C)		I <sub>TSM</sub>	126	А
Circuit Fusing Consideration (t = 8.3 ms)	l²t	66	A <sup>2</sup> sec	
Non-Repetitive Surge Peak Off-State Voltage ( $T_1 = 25^{\circ}C$ , t = 10 ms)		V <sub>DSM</sub> /V <sub>RSM</sub>	V <sub>DSM</sub> /V <sub>RSM</sub> +100	V
Peak Gate Current ( $T_J = 110^{\circ}$ C, t = 20µs)	I <sub>gm</sub>	4.0	W	
Peak Gate Power (Pulse Width $\leq$ 1.0 µs, T <sub>c</sub> = 80°C)	P <sub>GM</sub>	20	W	
Average Gate Power (T = 110°C)	P <sub>G(AV)</sub>	1.0	W	
Operating Junction Temperature Range	T <sub>j</sub>	-40 to +110	°C	
Storage Temperature Range	T <sub>stq</sub>	-40 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V<sub>DBM</sub> and V<sub>BBM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

## **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	1.8 60	°C/W
Maximum Lead Temperature for Soldering Purpose	s, 1/8" from case for 10 seconds	T,	260	°C

# **Electrical Characteristics - OFF** ( $TJ = 25^{\circ}C$ unless otherwise noted ; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T_ = 25°C	I <sub>DRM</sub> ,	-	-	0.005	mA
$(V_{D} = V_{DRM} = V_{RRM}; Gate Open)$	T_ = 110°C	I	-	-	1.0	ША

# **Electrical Characteristics - ON** ( $TJ = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Forward On-State Voltage (Note 2) ( $I_{TM} = \pm 17 \text{ A Peak}$ )		V <sub>TM</sub>	-	-	1.55	V
	MT2(+), G(+)		1.2	_	5.0	
Gate Trigger Current (Continuous dc) (V $_{\rm D}$ = 12 V, R $_{\rm L}$ = 30 $\Omega$ )	MT2(+), G(-)	I <sub>gt</sub>	1.2	-	5.0	mA
	MT2(-), G(-)		1.2	-	5.0	
Holding Current ( $V_D = 12$ V, Gate Open, Initiating Current = ±100 mA)		I <sub>H</sub>	-	-	10	mA
	MT2(+), G(+)		-	-	15	
Latching Current ( $V_p = 1.2 \text{ V}$ , $I_g = 7.5 \text{ mA}$ )	MT2(+), G(-)	Ι	-	-	15	mA
	MT2(-), G(-)		-	-	15	
	MT2(+), G(+)		0.5	-	1.3	
Gate Trigger Voltage (V $_{\rm D}$ = 12 V, R $_{\rm L}$ = 30 $\Omega$ )	MT2(+), G(-)	V <sub>gt</sub>	0.5	-	1.3	V
	MT2(-), G(-)		0.5	-	1.3	
	MT2(+), G(+)		0.2	_	_	
Gate Non–Trigger Voltage (T <sub>1</sub> = 110°C)	MT2(+), G(-)	$V_{gD}$	0.2	_	_	V
	MT2(-), G(-)		0.2	-	-	

2. Indicates Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%



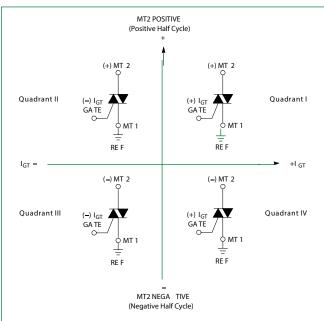
#### Thyristors Datasheet

## **Dynamic Characteristics**

Characteristic	Symbol	Min	Тур	Мах	Unit
Rate of Change of Commutating Current, See Figure 10. (Gate Open, T <sub>J</sub> = 125°C, No Snubber)	(dl/dt)c	1.75	_	-	A/ms
Critical Rate of Rise of On–State Current ( $T_J = 125^{\circ}C$ , f = 120 Hz, $I_G = 2 \times I_{GT}$ , tr $\leq 100$ ns)	dl/dt	-	_	45	A/µs
Critical Rate of Rise of Off-State Voltage (V <sub>D</sub> = 0.66 x V <sub>DRM</sub> , Exponential Waveform, Gate Open, T <sub>J</sub> = 125°C)	dV/dt	10	_	-	V/µs

## **Voltage Current Characteristic of SCR**

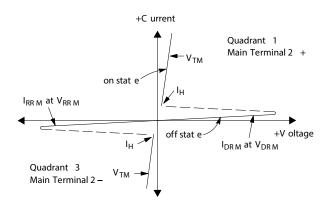
Symbol	Parameter
V <sub>drm</sub>	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current



**Quadrant Definitions for a Triac** 

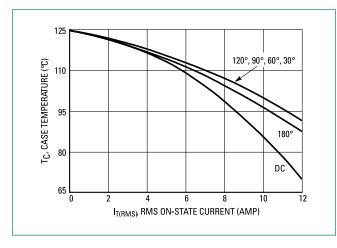
All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used



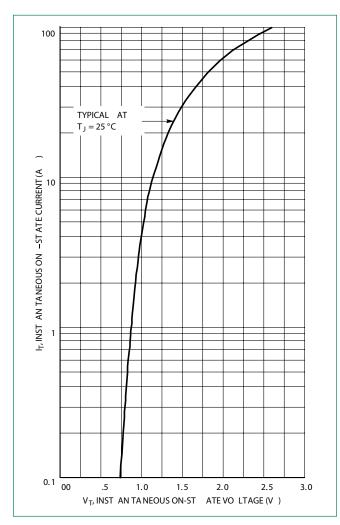


#### Thyristors Datasheet

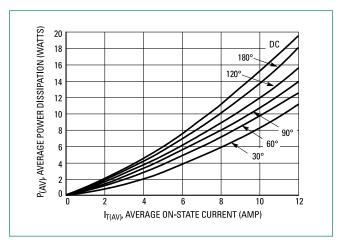


#### Figure 1. RMS Current Derating

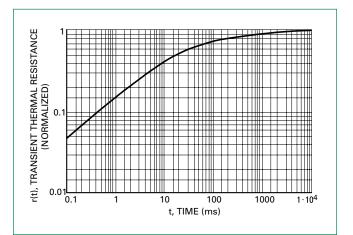
#### Figure 3. On–State Characteristics



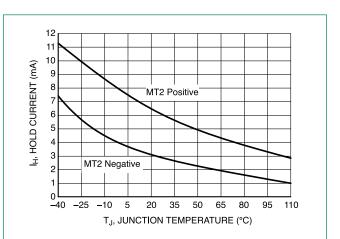
#### Figure 2. On-State Power Dissipation

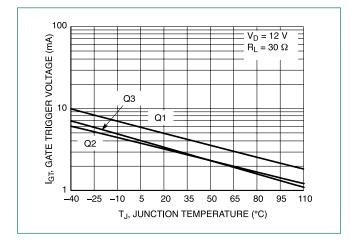


#### **Figure 4. Thermal Response**



#### **Figure 5. Typical Hold Current Variation**





**Figure 8. Typical Latching Current Variation** 

#### Figure 6. Typical Gate Trigger Current Variation

Figure 7. Typical Gate Trigger Voltage Variation

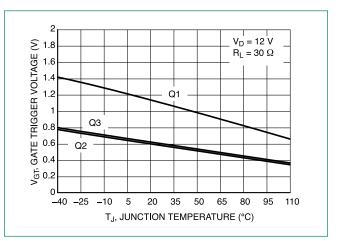
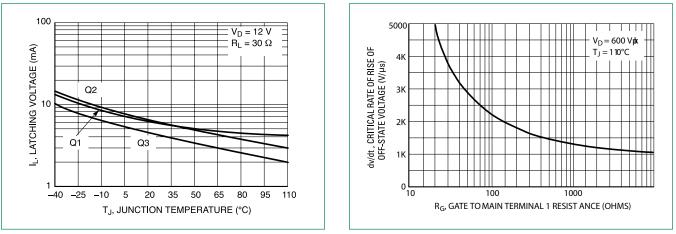
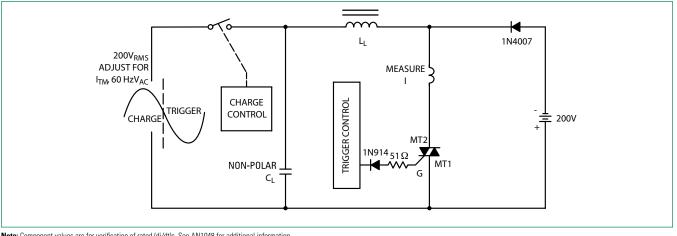


Figure 9. Critical Rate of Rise of Off-State Voltage (Exponential Waveform)





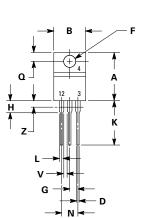


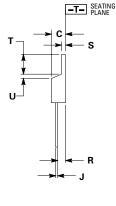
Note: Component values are for verification of rated (di/dt)c. See AN1048 for additional information



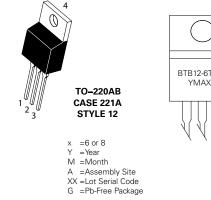
# BTB12-600TW3G Surface Mount – 600V

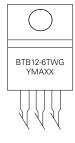
## **Dimensions**





### **Part Marking System**





Dim	Inches		Millimeters		
Dim	Min	Мах	Min	Мах	
Α	0.590	0.620	14.99	15.75	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.41	2.67	
н	0.110	0.130	2.79	3.30	
J	0.018	0.024	0.46	0.61	
К	0.540	0.575	13.72	14.61	
L	0.060	0.075	1.52	1.91	
Ν	0.195	0.205	4.95	5.21	
٥	0.105	0.115	2.67	2.92	
R	0.085	0.095	2.16	2.41	
S	0.045	0.060	1.14	1.52	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045	-	1.15	-	
Z	-	0.080	-	2.04	

Pin Assignment			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	No Connection		

## **Ordering Information**

Device	Package	Shipping
BTB12-600TW3G	TO-220AB (Pb-Free)	1000 Units / Box

1. Dimensioning and tolerancing per ansi y14.5m, 1982.

Controlling dimension: inch.
Dimension z defines a zone where all body and lead irregularities are allowed.

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